

the gate insulator layer (23) over the gate conductor layer;  
and

the silicon layer (24,26) over the gate insulator layer and  
defining the semiconductor channel overlying the gate conductors.

20. (amended) A device as claimed in claim 17, wherein the  
metallic layer is on top of the portion of the transparent  
conductor.

21. (amended) A device as claimed in claim 17, wherein a  
photoresist layer is on top of the portion of the transparent  
conductor.

22. (amended) A device as claimed in claim 17 comprising the  
active plate of an active matrix liquid crystal display.

#### REMARKS

The foregoing amendments to the claims were made solely to  
avoid filing the claims in the multiple dependent form so as to  
avoid the additional filing fee.

The claims were not amended in order to address issues of  
patentability and Applicants respectfully reserve all rights they  
may have under the Doctrine of Equivalents. Applicants furthermore

reserve their right to reintroduce subject matter deleted herein at a later time during the prosecution of this application or continuing applications.

Respectfully submitted,



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## APPENDIX

3. (amended) A method as claimed in claim 1 ~~or 2~~, wherein the electroplated areas comprise edge regions of the line conductors.

7. (amended) A method as claimed in ~~any preceding claim~~ claim 1, wherein the selectivity of the plating is achieved using a printed shielding layer.

10. (amended) A method as claimed in ~~any preceding claim~~ claim 1, wherein the metallic layer comprises copper or silver.

11. (amended) A method as claimed in ~~any preceding claim~~ claim 1, wherein the transparent conductor layer is pretreated before plating.

12. (amended) A method as claimed in ~~any preceding claim~~ claim 1, wherein the transparent conductor layer comprises a conductive oxide.

15. (amended) A method as claimed in ~~any preceding claim~~ claim 1, wherein the gate conductor (42) is deposited and patterned with a first lithographic process and the transparent conductor layer

defining source and drain conductors (28,30) and pixel electrodes (38) is deposited and patterned with a second lithographic process, the silicon layer being self aligned to the gate conductor.

16. (amended) A method as claimed in ~~any preceding claim~~ claim 1 for forming the active plate of an active matrix liquid crystal display.

19. (amended) A device as claimed in claim 17-~~or 18~~, comprising:  
a gate conductor layer (40) over an insulating substrate defining the gate conductors and also defining row conductors;  
the gate insulator layer (23) over the gate conductor layer;  
and  
the silicon layer (24,26) over the gate insulator layer and defining the semiconductor channel overlying the gate conductors.

20. (amended) A device as claimed in claim 17,~~18 or 19~~, wherein the metallic layer is on top of the portion of the transparent conductor.

21. (amended) A device as claimed in ~~any one of claims 17 to 20~~ claim 17, wherein a photoresist layer is on top of the portion of the transparent conductor.

22. (amended) A device as claimed in ~~any one of claims 17 to 21~~  
claim 17 comprising the active plate of an active matrix liquid  
crystal display.

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